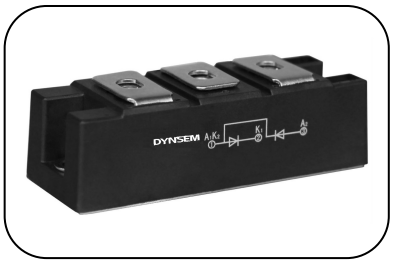
DSKD110 DSND110 DSMD110 DSKE110
Diode Modules



DSPACK 2

Features：

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- Various rectifiers
- DC supply for PWM inverter

V_{DSM},V_{RSM}	V_{DRM},V_{RRM}	Type & Outline
2700V	2600V	DSxx110/26-216F3
2900V	2800V	DSxx110/28-216F3
3100V	3000V	DSxx110/30-216F3
3300V	3200V	DSxx110/32-216F3
3500V	3400V	DSxx110/34-216F3
3700V	3600V	DSxx110/36-216F3

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100°C	150			110	A
$I_{F(RMS)}$	RMS forward current		150			173	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			20	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}	150			2.10	kA
I^2t	I^2t for fusing coordination					22	A^2s*10^3
V_{FO}	Threshold voltage		150			0.95	V
r_F	Forward slope resistance					1.76	mΩ
V_{FM}	Peak forward voltage	I_{FM}=330A	25			2.25	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180^0 sine Single side cooled per chip				0.31	°C /W
$R_{th(c-h)}$	Thermal resistance case to heatsink	At 180^0 sine Single side cooled per chip				0.08	°C /W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min, I_{iso}:1mA(max)		4000			V
F_m	Terminal connection torque(M6)				6.0		N·m
	Mounting torque(M6)				6.0		N·m
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				320		g
Outline	DSPACK 2						

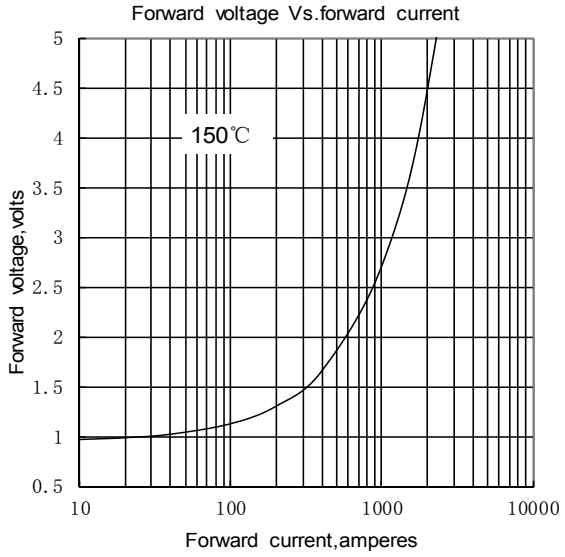


Fig.1

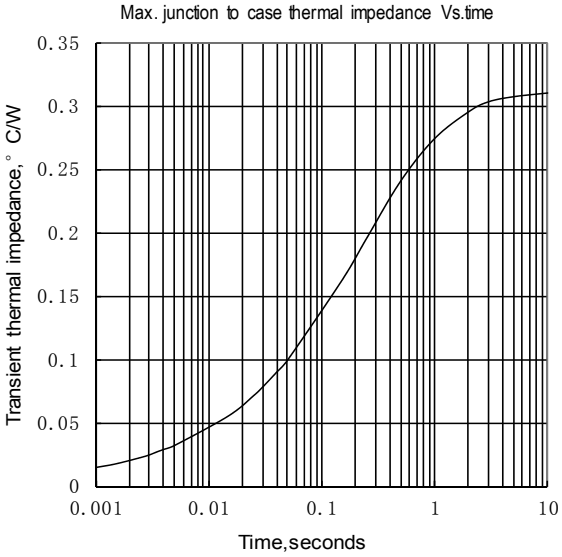


Fig.2

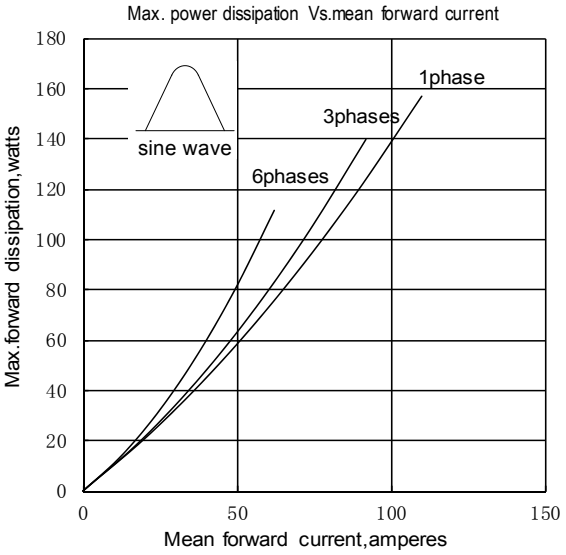


Fig.3

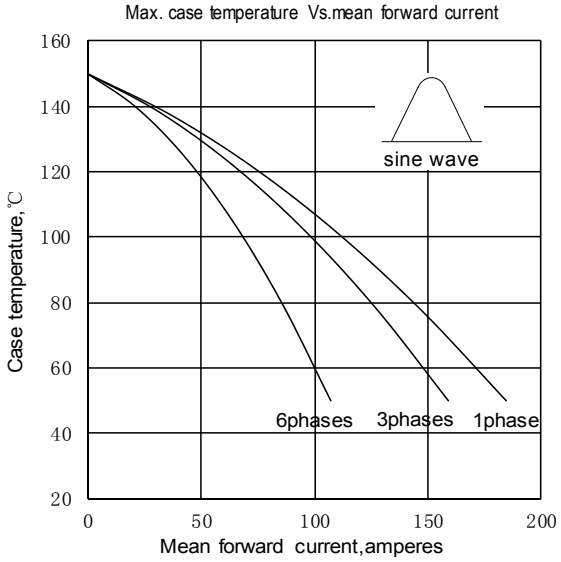


Fig.4

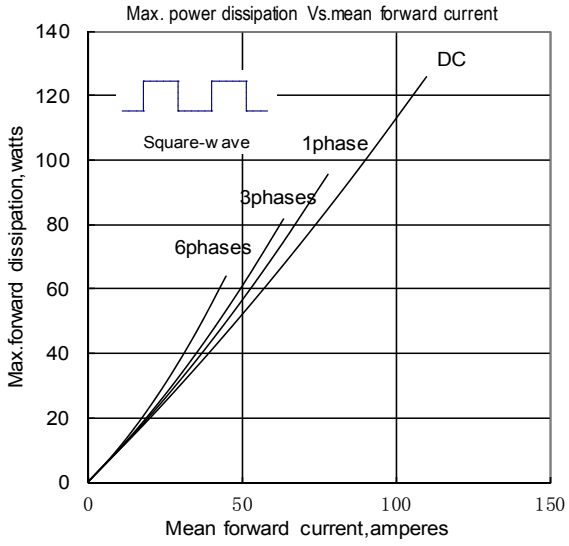


Fig.5

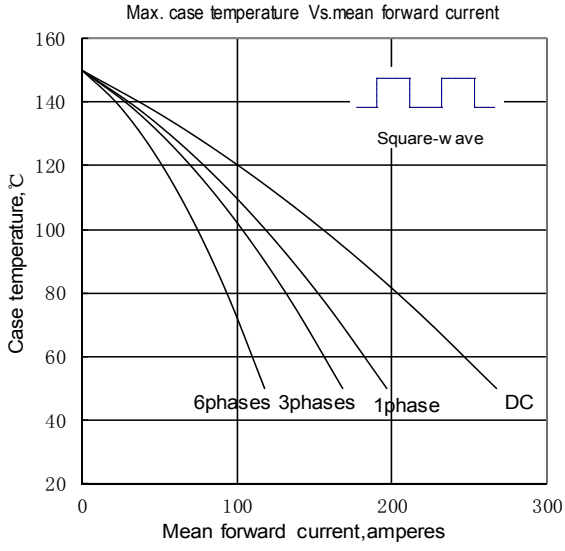


Fig.6

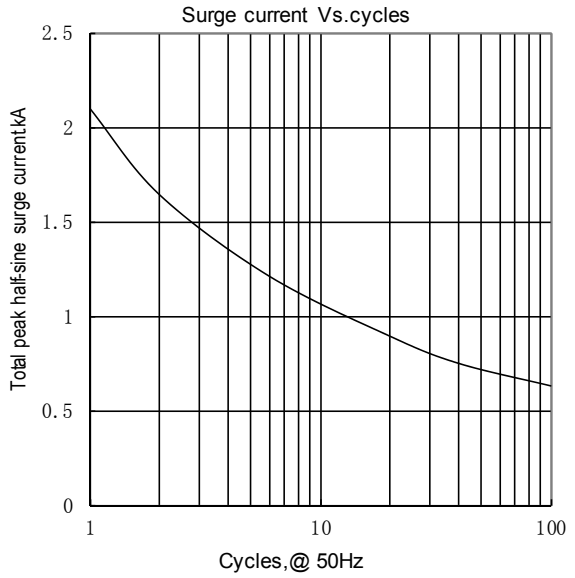


Fig.7

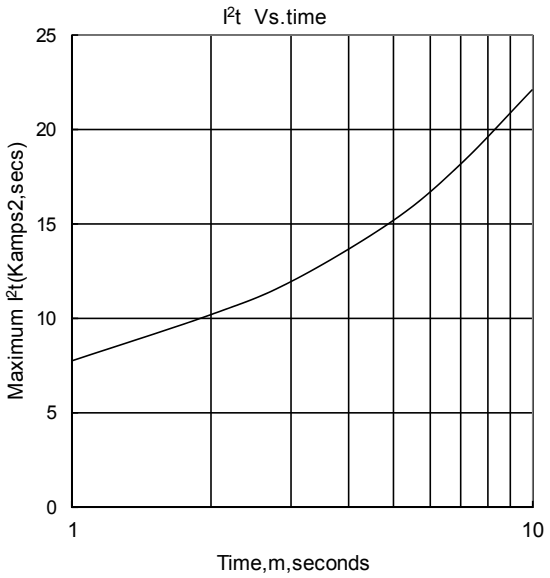
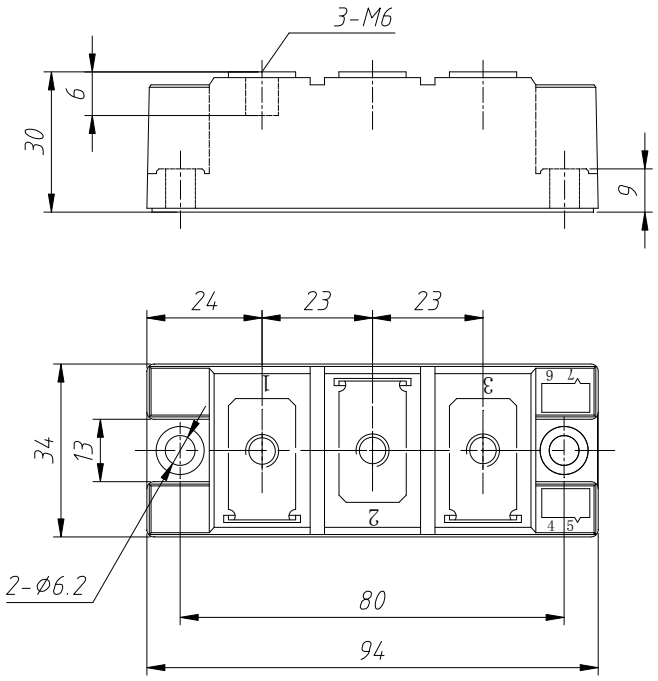


Fig.8

Outline:



DSPACK 2